



FEATURES

- N-Channel JFET Amplifiers
- N-Channel JFET Switches
- P-Channel JFETs
- Dual N-Channel JFETs
- N-Channel Lateral DMOS FETs
- N-Channel Enhancement Mode MOSFET Transistors
- P-Channel Enhancement Mode MOSFET Transistors
- Current Regulator Diodes
- Low-Leakage Diodes
- Voltage Controlled Resistors

BREAKDOWN		I_{DSS}		g_{fs}		$V_{GS(off)}$		GATE LEAKAGE		$r_{DS(on)}$		C_{iss}		COMMENTS
VOLTAGE		(mA)		(mS)		(V)		(pA)		Typ.		(pF)		
TYPE	MIN.(V)	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	(W)		TYP.	MAX.	
SSTD89A	N-CHANNEL JFET AMPLIFIERS SC-70-5 (SOT-353)													
	-15		1.1	0.7		-0.3	-1.2		100	-		3.8		Built-in Self-Biased Diodes
J204 2N3819 2N5484 2N5485 2N5486 J210 J211 J212 J308 J309 J310 J305 J304 PN4117A PN4118A PN4119A J201 J202	N-CHANNEL JFET AMPLIFIERS TO-226AA (TO-92)													
	-25	0.2	3	0.5		-0.3	-2	-2	-100	450	4.5	—		Low Noise/Low Voltage
	-25	2	20	2	6.5		-8	-2	-2000	150	—	8		High Frequency
	-25	1	5	3	6	-0.3	-3	-2	-1000	300	—	5		High Freq/ Gen. Purpose
	-25	4	10	3.5	7	-0.5	-4	-2	-1000	175	—	5		High Freq/Gen. Purpose
	-25	8	20	4	8	-2	-6	-2	-1000	110	—	5		High Freq/Gen. Purpose
	-25	2	15	4	12	-1	-3	-1	-100	140	4	—		High Frequency
	-25	7	20	6	12	-2.5	-4.5	-1	-100	100	4	—		High Frequency
	-25	15	40	7	12	-4	-6	-1	-100	70	4	—		High Frequency
	-25	12	60	8	—	-1	-6.5	-2	-1000	35	—	5		Very High Frequency
	-25	12	30	10	—	-1	-4	-2	-1000	45	—	5		Very High Frequency
	-25	24	60	8	—	-2	-6.5	-2	-1000	35	—	5		Very High Frequency
	-30	1	8	3	—	-0.5	-3	-2	-100	200	2.2	—		High Frequency
	-30	5	15	4.5	7.5	-2	-6	-2	-100	150	2.2	—		High Frequency
	-40	0.03	0.09	0.07	0.21	-0.6	-1.8	-0.2	-1	11000	—	3		Ultralow Leakage
	-40	0.08	0.24	0.08	0.25	-1	-3	-0.2	-1	7000	—	3		Ultralow Leakage
	-40	0.2	0.6	0.1	0.33	-2	-6	-0.2	-1	4500	—	3		Ultralow Leakage
	-40	0.2	1	0.5	—	-0.3	-1.5	-2	-100	750	4.5	—		Low Noise/Low Voltage
-40	0.9	4.5	1	—	-0.8	-4	-2	-100	400	4.5	—		Low Noise	
SST204 SST5484 SST5485 SSTJ211 SST5486 SST308 SST309 SSTJ212 SST310 SST4416 SST4117 SST4118 SST4119 SST201 SST202	N-CHANNEL JFET AMPLIFIERS TO-236 (SOT-23)													
	-25	0.2	3	0.5	—	-0.33	-2	-2	-100	450	2.2	—		Low Noise/Low Voltage
	-25	1	5	3	6	-0.3	-3	-2	-1000	300	5	—		High Freq/Gen. Purpose
	-25	4	10	3.5	7	-0.5	-4	-2	-1000	175	5	—		High Freq/Gen. Purpose
	-25	7	20	6	12	-25	45	-1	-100	100	4**	—		High Frequency Amplifier
	-25	8	20	4	8	-2	-6	-2	-1000	110	5	—		High Freq/Gen. Purpose
	-25	12	60	8	—	-1	-6.5	-2	-1000	35	5	—		Very High Freq.
	-25	12	30	8	—	-1	-4	-2	-1000	45	5	—		Very High Freq.
	-25	15	40	7	12	-4	-6	-1	-100	70	4**	—		High Frequency Amplifier
	-25	24	60	8	—	-2	-6.5	-2	-1000	35	5	—		Very High Frequency
	-30	5	15	4.5	7.5		-6	-2	-1000	150	4	—		Low Noise/High Freq.
	-40	0.03	0.09	0.07	0.21	-0.6	-1.8	-0.2	-10	11000	3	—		Very Low Leakage
	-40	0.08	0.24	0.08	0.25	-1	-3	-0.2	-10	7000	3	—		Very Low Leakage
	-40	0.2	0.6	0.1	0.33	-2	-6	-0.2	-10	4500	3	—		Very Low Leakage
	-40	0.2	1	0.5	—	-0.3	-1.5	-2	-100	750	4.5	—		Low Noise/Low Voltage
	-40	0.9	4.5	1	—	-0.8	-4	-2	-100	400	4.5	—		Low Noise

*Typical

BREAKDOWN VOLTAGE		I_{DSS} (mA)		g_{fs} (mS)		$V_{GS(off)}$ (V)		GATE LEAKAGE (pA)		$r_{DS(on)}$ TYP. (Ω)	C_{iss} (pF)		COMMENTS
TYPE	MIN. (V)	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.		
N-CHANNEL JFET AMPLIFIERS TO-206AA (TO-18), TO-206AC (TO-52), TO-206AF (TO-72)													
U309	-25	12	30	10	—	-1	-4	-2	-150	45	—	5	Very High Freq.
U310	-25	24	60	10	—	-2.5	-6	-2	-150	45	—	5	Very High Freq.
2N4416	-30	5	15	4.5	7.5	—	-6	-2	-100	150	—	4	Low Noise/High Freq.
2N4416A	-35	5	15	4.5	7.5	-2.5	-6	-2	-100	150	—	4	Low Noise/High Freq.
2N4117A	-40	0.03	0.09	0.07	0.21	-0.6	-1.8	-0.2	-1	11000	—	3	Ultralow Leakage
2N4118A	-40	0.08	0.24	0.08	0.25	-1	-3	-0.2	-1	7000	—	3	Ultralow Leakage
2N4119A	-40	0.2	0.6	0.1	0.33	-2	-6	-0.2	-1	4500	—	3	Ultralow Leakage
2N4338	-50	0.2	0.6	0.6	1.8	-0.3	-1	-2	-100	—	2500	7	Low Noise/Low Voltage
2N4339	-50	0.5	1.5	0.8	2.4	-0.6	-1.8	-2	-100	—	1700	7	Low Noise/Low Voltage
2N4340	-50	1.2	3.6	1.3	3	-1	-3	-2	-100	—	1500	7	Low Noise
2N4341	-50	3	9	2	4	-2	-6	-2	-100	—	800	7	Low Noise

BREAKDOWN VOLTAGE		$r_{DS(on)}$ MAX.	$V_{GS(off)}$ (V)		I_{DSS} (mA)		GATE LEAKAGE (pA)		g_{fs} TYP. (mS)			C_{iss} MAX. (pF)
TYPE	MIN. (V)	(Ω)	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	$I_D =$ 1 mA	$I_D =$ 10 mA	$I_D =$ 25 mA	
N-CHANNEL JFET SWITCHES TO-226AA (TO-92)												
J105	-25	3	-4.5	-10	500	—	-20	-3000	—	—	55	160
J106	-25	6	-2	-6	200	—	-20	-3000	—	—	55	160
J107	-25	8	-0.5	-4.5	100	—	-20	-3000	—	—	55	160
J108	-25	8	-3	-10	80	—	-10	-3000	—	17	—	85
J109	-25	12	-2	-6	40	—	-10	-3000	—	17	—	85
J110	-25	18	-0.5	-4	10	—	-10	-3000	—	17	—	85
J111	-35	30	-3	-10	20	—	-5	-1000	6	—	—	12
J112	-35	50	-1	-5	5	—	-5	-1000	6	—	—	12
J113	-35	100	—	-3	2	—	-5	-1000	6	—	—	12
PN4391	-40	30	-4	-10	50	150	-5	-1000	6	—	—	16
PN4392	-40	60	-2	-5	25	100	-5	-1000	6	—	—	16
PN4393	-40	100	-0.5	-3	5	60	-5	-1000	6	—	—	16

N-CHANNEL JFET SWITCHES TO-236 (SOT-23)												
SST108	-25	8	-3	-10	80	—	-10	-3000	—	17	—	85
SST109	-25	12	-2	-6	40	—	-10	-3000	—	17	—	85
SST110	-25	18	-0.5	-4	10	—	-10	-3000	—	17	—	85
SST111	-35	30	-3	-10	20	—	-5	-1000	6	—	—	12
SST4391	-35	30	-4	-10	50	—	-5	-100	6	—	—	16
SST112	-35	50	-1	-5	5	—	-5	-1000	6	—	—	12
SST4392	-35	60	-2	-5	25	—	-5	-100	6	—	—	16
SST113	-35	100	—	-3	2	—	-5	-1000	6	—	—	12
SST4393	-35	100	-0.5	-3	5	—	-5	-100	6	—	—	16



BREAKDOWN			GATE LEAKAGE						g _{fs} TYP. (mS)			C _{iss}	
TYPE	VOLTAGE	r _{DS(on)} MAX.	V _{GS(off)} (V)		I _{DSS} (mA)		(pA)		I _D =	I _D =	I _D =	C _{iss} MAX.	
	MIN. (V)	(Ω)	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	1 mA	10 mA	25 mA	(pF)	
	N-CHANNEL JFET SWITCHES TO-206AA (TO-18), TO-206AC (TO-52)												
2N5432	-25	5	-4	-10	150	—	-5	-200	—	17	—	30	
2N5433	-25	7	-3	-9	100	—	-5	-200	—	17	—	30	
2N5434	-25	10	-1	-4	30	—	-5	-200	—	17	—	30	
2N4859JAN/TX/TXV	-30	25	-4	-10	50	—	-5	-250	—	—	—	18	
2N4860JAN/TX/TXV	-30	40	-2	-6	20	100	-5	-250	—	—	—	18	
2N4861JAN/TX/TXV	-30	60	-0.8	-4	8	80	-5	-250	—	—	—	18	
2N4856A	-40	25	-4	-10	50	—	-5	-250	6	—	—	10	
2N4856JAN/TX/TXV	-40	25	-4	-10	50	—	-5	-250	—	—	—	18	
2N4391	-40	30	-4	-10	50	150	-5	-100	6	—	—	14	
2N4857A	-40	40	-2	-6	20	100	-5	-250	6	—	—	10	
2N4857JAN/TX/TXV	-40	40	-2	-6	20	100	-5	-250	—	—	—	18	
2N4392	-40	60	-2	-5	25	75	-5	-100	6	—	—	14	
2N4858A	-40	60	-0.8	-4	8	80	-5	-250	6	—	—	10	
2N4858JAN/TX/TXV	-40	60	-0.8	-4	8	80	-5	-250	—	—	—	18	
2N4393	-40	100	-0.5	-3	5	30	-5	-100	6	—	—	14	
	BREAKDOWN												
TYPE	VOLTAGE		r _{DS(on)}		V _{GS(off)} (V)		I _{DSS} (mA)		g _{FS} (mS)		GATE LEAKAGE		C _{iss}
	MIN. (V)	MAX. (Ω)	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	TYP. (pF)
	P-CHANNEL JFETs TO-226AA (TO-92)												
J270	30	—	0.5	2	-2	-15	6	15	10	200	20		
J271	30	—	1.5	4.5	-6	-50	8	18	10	200	20		
2N5460	40	—	0.75	6	-1	-5	1	4	3	5000	4.5		
2N5461	40	—	1	7.5	-2	-9	1.5	5	3	5000	4.5		
2N5462	40	—	1.8	9	-4	-16	2	6	3	5000	4.5		
P1086	30	75	10	-10	—	—	*4.5	—	10	2000	20		
J174	30	85	5	10	-20	-135	*4.5	—	10	1000	20		
J175	30	125	3	6	-7	-70	*4.5	—	10	1000	20		
P1087	30	150	5	-5	—	—	*4.5	—	10	2000	20		
J176	30	250	1	4	-2	-35	*4.5	—	10	1000	20		
J177	30	300	0.8	2.25	-1.5	-20	*4.5	—	10	1000	20		
	P-CHANNEL JFETs TO-236 (SOT-23)												
SST270	30	—	0.5	2	-2	-15	6	15	10	200	20		
SST271	30	—	1.5	4.5	-6	5	8	18	10	200	20		
SST174	30	85	5	10	-20	-135	*4.5	—	10	1000	20		
SST175	30	125	3	6	-7	-70	*4.5	—	10	1000	20		
SST176	30	250	1	4	-2	-35	*4.5	—	10	1000	20		
SST177	30	300	0.8	2.25	-1.5	-20	*4.5	—	10	1000	20		
SST5460	40	—	0.75	6	-1	-5	1	4	3	5000	4.5		
SST5461	40	—	1	7.5	-2	-9	1.5	5	3	5000	4.5		
SST5462	40	—	1.8	9	-4	-16	2	6	3	5000	4.5		

BREAKDOWN											C _{iss} TYP. (pF)	
TYPE	VOLTAGE	r _{DS(on)}	V _{GS(off)} (V)		I _{DSS} (mA)		GATE LEAKAGE (pA)		g _{FS} (mS)			
	MIN. (V)	MAX. (Ω)	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	TYP.			
	P-CHANNEL JFETs TO-206AA (TO-18)											
2N5114	30	75	5	10	-30	-90	5	500	*4.5	20		
2N5114*	30	75	5	10	-30	-90	5	500	*4.5	20		
2N5115	30	100	3	6	-15	-60	5	500	*4.5	20		
2N5115*	30	100	3	6	-15	-60	5	500	*4.5	20		
2N5116	30	150	1	4	-5	-25	5	500	*4.5	20		
2N5116*	30	150	1	4	-5	-25	5	500	*4.5	20		
*JAN/JANTX/TXV	Typical Value at V _{DS} = -15 V, I _D = -1 mA. Equivalent device numbers from other supplier in parenthesis.											
TYPE	BREAKDOWN		(V _{GS1} -V _{GS2})	GATE		gfs (mS)		V _{GS(off)}		C _{iss}	PACKAGE	COMMENTS
	VOLTAGE	Max.	DRIFT	LEAKAGE			I _{DSS} (mA)		MAX.	MAX.		
	MIN. (V)	(MV)	(MV/°C)	MAX. (PA)	MIN.	MAX.	MIN.	MAX.	(V)	(pF)		
	DUAL N-CHANNEL JFETs											
SST404	-40	15	25	-15	1	2	0.5	10	-2.5	8	SO-8	Low Noise
SST406	-40	40	80	-15	1	2	0.5	10	-2.5	8	SO-8	High Gain/Freq.
SST441	-25	20	*10	-500	4.5	9	6	30	-6	*3.5	SO-8	High Gain/Freq.
U401	-40	5	10	-15	1	2	0.5	10	-2.5	8	TO-71	Low Noise
U404	-40	15	25	-15	1	2	0.5	10	-2.5	8	TO-71	Low Noise
U406	-40	40	80	-15	1	2	0.5	10	-2.5	8	TO-71	Low Noise
U421	-40	10	10	-0.25	0.12	0.35	0.06	1	-2	3	TO-78	Ultra Low Leakage
U423	-40	25	40	-0.25	0.12	0.35	0.06	1	-2	3	TO-78	Ultra Low Leakage
U430	-25	*25		*-15	10	—	12	30	-4	5	TO-78	High Freq/Low Noise
U431	-25	*25		*-15	10	—	24	60	-6	5	TO-78	High Freq/Low Noise
U440	-25	10	*20	-500	4.5	9	6	30	-6	*3	TO-71	High Gain
U441	-25	20	*20	-500	4.5	9	6	30	-6	*3	TO-71	High Gain
2N3958	-50	25	100	-50	1	3	0.5	5	-4.5	4	TO-71	Tight Match/Low IG
2N5196	-50	5	5	-15	0.7	1.6	0.7	7	-4	6	TO-71	Tight Match/Low IG
2N5197	-50	5	10	-15	0.7	1.6	0.7	7	-4	6	TO-71	Tight Match/Low IG
2N5198	-50	10	20	-15	0.7	1.6	0.7	7	-4	6	TO-71	General Purpose
2N5199	-50	15	40	-15	0.7	1.6	0.7	7	-4	6	TO-71	General Purpose
2N5545JAN/ JANTX/TXV	-50	5	10	-50	1.5	6	0.5	8	-4.5	6	TO-71	Military Hi-Rel
2N5546JAN/ JANTX/TXV	-50	10	20	-50	1.5	6	0.5	8	-4.5	6	TO-71	Military Hi-Rel
2N5547JAN/ JANTX/TXV	-50	15	40	-50	1.5	6	0.5	8	-4.5	6	TO-71	Military Hi-Rel
2N5564JAN	-40	5	10	*-3	7.5	12.5	5	30	-3	12	TO-71	High Gain
2N5565JAN	-40	10	25	*-3	7.5	12.5	5	30	-3	12	TO-71	High Gain
2N5566JAN	-40	20	50	*-3	7.5	12.5	5	30	-3	12	TO-71	High Gain
2N5911JAN	-25	10	20	-100	5	10	7	40	-5	5	TO-78	High Gain
2N5912JAN	-25	15	40	-100	5	10	7	40	-5	5	TO-78	High Gain



TYPE	$V_{(BR)DS}$ MIN. (V)	$V_{(BR)SD}$ MIN. (V)	$r_{DS(on)}$ TYP. (Ω)	t_r MAX. (ns)	$V_{GS(off)}$ (V) MIN.	MAX.	PACKAGE	COMMENTS
SD210DE-2 SD211DE-2 SD213DE-2 SD214DE-2 SD215DE-2	N-CHANNEL LATERAL DMOS FETs Configuration - Single							
	30	10	30	1	0.5	1.5	TO-206AF	
	30	10	30	1	0.5	1.5	TO-206AF	Zenered Gate
	10	10	30	1	0.1	1.5	TO-206AF	Zenered Gate
	20	20	30	1	0.1	1.5	TO-206AF	
	20	20	30	1	0.1	1.5	TO-206AF	Zenered Gate
SD50001-2	N-CHANNEL LATERAL DMOS FETs Configuration - Quad							
	20	20	30	1	0.1	1.5	16-Pin Siderbraz	Zenered Gate
TYPE	$V_{(BR)DSS}$ MIN. (V)	$r_{DS(on)}$ MAX. (Ω)	$V_{GS(th)}$ MAX. (V)	t_{ON} MAX. (ns)	C_{iss} TYP. (pF)	I_D MAX. (A)	P_D MAX. (W)	
VQ1001J VQ1001P VQ1004J VQ1004P VQ1000J VQ1000P VQ1006P	N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS 14-Pin Sidebraz (P) and Plastic (J)							
	30	1	2.5	30	38	3	2	
	30	1	2.5	30	38	3	2	
	60	3.5	2.5	10	35	0.46	1.3	
	60	3.5	2.5	10	35	0.46	1.3	
	60	5.5	2.5	10	22	1	1.3	
	60	5.5	2.5	10	22	1	1.3	
	90	4.5	2.5	10	35	2	2	
2N6660JANTX 2N6660 2N6661JANTX 2N6661	N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS TO-205AD (TO-39)							
	60	3	2	10	35	3	6.25	
	60	3	2	10	35	3	6.25	
	90	4	2	10	35	3	6.25	
	90	4	2	10	35	3	6.25	
VN66AFD VN88AFD VN2406D	N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS TO-220/TO-220SD							
	60	3	2.5	15	35	3	15	
	80	4	2.5	15	35	3	15	
	240	6	2	16	110	3	20	
VN10LE	N-CHANNEL ENHANCEMENT MODE MOSFET TRANSISTORS TO-206AC (TO-52)							
	60	5	2.5	10	22	1	1.5	

TYPE	$V_{(BR)DSS}$ MIN. (V)	$r_{DS(on)}$ MAX. (Ω)	$V_{GS(th)}$ MAX. (V)	t_{ON} MAX. (ns)	C_{ISS} TYP. (pF)	I_D MAX. (A)	P_D MAX. (Ω)
N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS TO-226AA (TO-92)							
TN0201L	60	3	2	10	35	1.6	0.8
VN0300L	30	1.2	2.5	30	38	3	0.8
TN0401L	40	1.2	2	30	38	1.5	0.8
TN0601L	60	1.8	2	15	35	1.5	0.8
VN0606L	60	3	2	10	35	1.6	0.8
2N7000	60	5	3	10	20	0.5	0.4
VN0610L	60	5	2.5	10	38	1	0.8
BS170	60	5	3	10	22	0.8	0.83
VN0610LL	60	5	2.5	10	22	1.3	0.8
VN2222LL	60	7.5	2.5	10	22	1	0.8
VN2222L	60	7.5	2.5	10	38	1	0.8
VN0808L	80	4	2	10	35	1.9	0.8
VN1206L	120	6	2	16	35	2	0.8
VN2010L	200	10	1.8	20	35	0.8	0.8
BS107	200	28	3	5	35	—	0.5
VN2406L	240	6	2	16	115	1.7	0.8
VN2410L	240	10	2	16	115	1.7	0.8
TN2410L	240	10	1.8	35	110	1	0.8
TN2460L	240	60	1.8	20	14	0.8	0.8
TN3012L	300	12	3	50	40	0.5	0.8
VN3515L	350	15	1.8	40	85	0.6	0.8
VN4012L	400	12	1.8	40	85	0.65	0.8
VN50300L	500	300	4.5	20	5	0.13	0.8
N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS TO-92S							
VN0300LS	30	1-2	2-5	30	38	3	0.9
VN10KLS	60	5	2-5	10	30	1	0.9
VN10LLS	60	5	2-5	10	22	1.4	0.9
VN0808LS	80	4	2	10	35	1.9	0.9
VN2410LS	240	10	2	16	110	2	0.9
N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS (Super SOT-23)							
TN0200TS	20	0.4	0.9*	34	90	9	1
N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS TO236 (SOT-23)							
TN0200T	20	0.4	0.9*	34	90	4	35
TN0201T	20	1	3	15*	65	0.75	0.2
2N7002K	60	2	2.5	25	30	0.3	0.35
VN0605T	60	5	3	20	22	0.72	0.36
2N7002	60	7.5	2.5	20	22	0.8	0.2
2N7002E	60	3	2.5	20	25	1.3	0.35
TN2010T	200	11	3	20*	35	0.085	0.2
TN2460T	240	60	1.8	20	14	0.4	0.36
VN50300T	500	300	4.5	20	5	0.08	0.35
N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS SC-70 3 LEADS (Single)							
Si1300DL	20	2.50	2.5	—	0.35	0.25	0.15
TN0205A	20	2.50	2.5	—	0.35	0.25	0.15
Si1304DL	25	0.45	2.5	—	1.85	0.75	0.33
Si1302DL	30	0.7	4.5	—	0.86	0.64	0.31



TYPE	V_{DS} (V)	$r_{DS(on)}$ (Ω) MAX.	$V_{GS(th)}$ MAX. (V)	t_{ON} (ns) MAX.	Q_g (nC) TYP.	I_D MAX. (A)	P_D MAX. (W)
N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-70 6 LEADS (Dual)							
Si1410EDH	20	0.10	1.8	—	5.6	3.7	1.56
Si1400DL	20	0.23	2.5	—	2.1	1.7	0.63
Si1912EDH	20	0.45	1.8	—	0.65	1.28	0.74
Si1902DL	20	0.63	2.5	—	0.8	0.7	0.3
Si1906DL	20	2.50	2.5	—	0.35	0.25	0.2
TN0205AD	20	2.50	2.5	—	0.35	0.25	0.20
Si1904EDH	25	1.04	2.5	—	0.66	0.73	0.74
Si1900DL	30	0.7	4.5	—	0.86	0.64	0.3
N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-75A							
Si1012R	20	1.25	1.8	15	60	0.5	0.15
Si1032R	20	9	1.8	15	60	0.2	0.28
Si1022R	60	3	4.5	25	30	0.33	0.25
N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-89 (3 LEADS)							
Si1012X	20	1.25	1.8	15	60	0.5	0.25
Si1032X	20	9	1.8	15	60	0.21	0.34
N-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-89 (6 LEADS)							
Si1024X	20	1.25	1.8	15	60	0.5	0.25
Si1034X	20	9	1.8	15	60	0.14	0.25
Si1026X	60	3	4.5	25	30	0.33	0.25
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
14-PIN SIDEBRAZE (P) and PLASTIC (J)							
VQ2001J	-30	2	-4.5	30	60	-2	2
VQ2001P	-30	2	-4.5	30	60	-2	2
VQ2004J	-60	5	-4.5	55	75	-3	2
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
TO-205AD (TO-39)							
VP0300B	-30	2.5	-4.5	30	60	-3	6.25
VP0808B	-80	5	-4.5	55	75	-3	6.25
VP1008B	-100	5	-4.5	55	75	-3	6.25
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
TO-226AA (TO-92)							
VP0300L	-30	2.5	-4.5	30	60	-2.4	0.8
BS250	-45	14	-3.5	10	15	—	0.83
VP0610L	-60	10	-3.5	25	15	-0.8	0.8
TP0610L	-60	10	-2.4	25	15	-0.8	0.8
VP0808L	-80	5	-4.5	55	75	-3	0.8
VP1008L	-100	5	-4.5	55	75	-3	0.8
BSS92	-200	20	-2.8	14	30	-0.6	1
VP2020L	-200	20	-2.5	25	30	-0.48	0.8
VP2410L	-240	10	-2.5	45	65	-0.72	0.8
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
TO-92S							
VP0300LS	-30	2-5	-9	30	60	-3	0-9
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
TO-236 (SOT-23)							
TP0101T	-20	0.65	-0.9*	47	110	-3	0.35
TP0101TS	-20	0.65	-0.9*	47	110	-3	1
TP0202T	-20	1.4	-3	42	55	-0.75	0.2
TP0202K	-0.3	3.5	-4.5	9	31	-0.385	0.35
TP0610K	-60	6	-10	20	23	-185	0.35
TP0610T	-60	10	-2.4	25	15	-0.4	0.36
VP0610T	-60	10	-3.5	25	15	-0.4	0.36
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-70 3 LEADS (Single)							
Si1305DL	5-8	0.53	-1.8	—	2.6	0.92	0.34
Si1307DL	-12	0.58	-1.8	—	3.2	0.91	0.34
Si1303DL	-20	0.70	-2.5	—	1.7	0.72	0.34
Si1301DL	-20	5.00	-2.5	—	0.35	0.18	0.15
TP0205A	-20	5.00	-2.5	—	0.3	0.18	0.15

*Typical

TYPE	$V_{(BR)DS}$ (V) MIN.	$r_{DS(on)}$ (Ω) TYP.	$V_{GS(th)}$ MAX. (V)	t_{ON} (ns) MAX.	C_{iss} TYP. (pF)	I_D MAX. (A)	P_D MAX. (W)
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-70 6 LEADS (Dual)							
Si1405DL	-8	0.21	-1.8	—	5.5	1.8	0.63
Si1905DL	-8	1.20	-1.8	—	1.5	0.6	0.3
Si1417EDH	-12	0.16	-1.8	—	5.8	3.3	1.56
Si1407DL	-12	0.22	-1.8	—	5.5	1.8	0.63
Si1917EDH	-12	0.80	-1.8	—	1.3	1.15	0.73
Si1907DL	-12	1.31	-1.8	—	1.5	0.56	0.3
Si1413EDH	-20	0.22	-1.8	—	5.6	2.9	1.56
Si1403DL	-20	0.26	-2.5	—	3.7	1.5	0.63
Si1913EDH	-20	1.10	-1.8	—	1.2	1.0	0.74
Si1903DL	-20	1.80	-2.5	—	1.2	0.44	0.3
Si1901DL	-20	5.00	-2.5	—	0.35	0.18	0.2
TP0205AD	-20	5.00	-2.5	—	0.3	0.18	0.20
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-75A							
Si1013R	-20	2.7	-1.8	15	70	-0.35	0.15
Si1031R	-20	15	-1.8	15	70	-0.15	0.28
Si1021R	-60	8	-4.5	20	23	-0.17	0.25
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-89 (3 Leads)							
Si1013X	-20	2.7	-1.8	15	70	-0.35	0.25
Si1031X	-20	15	-1.8	15	70	-0.165	0.34
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-89 (6 Leads)							
Si1023X	-20	2.7	-1.8	5	70	-0.4	0.25
Si1033X	-20	8	-1.8	15	70	-0.16	0.25
Si1025X	-60	8	-4.5	20	23	-0.19	0.25
P-CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
TO-206AF							
3N164	-30	300	-5	36	2.4	-0.05	0.375
3N163	-40	250	-5	36	2.4	-0.05	0.375
TYPE	V_{DS} (V)	$r_{DS(on)}$ (Ω) MAX.	$V_{GS(th)}$ MAX. (V)	t_{ON} (ns) MAX.	Q_g (nC) TYP.	I_D MAX. (A)	P_D MAX. (W)
N & P CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-70 6 LEADS (Complimentary)							
Si1555DL	20	0.63	2.5		0.8	0.7	0.3
	-8	0.85	-2.5		1.5	0.6	0.3
Si1563EDH	20	0.45	1.8		0.65	1.28	0.74
	-20	1.10	-1.8		1.2	1.00	0.3
Si1553DL	20	0.63	2.5		0.8	0.7	0.3
	-20	1.80	-2.5		1.2	0.44	0.3
Si1551DL	20	4.20	2.5		0.72	0.3	0.3
	-20	1.80	-2.5		0.52	0.44	0.3
Si1501DL	20	2.50	2.5		0.3	0.25	0.2
	-20	5.00	-2.5		0.3	0.18	0.2
TC0205AD	20	2.50	2.5		0.35	0.25	0.20
	-20	5.00	-2.5		0.35	0.18	0.20
Si1539DL	30	0.7	4.5		0.86	0.63	0.3
	-30	1.7	-4.5		0.90	0.45	0.3



N & P CHANNEL ENHANCEMENT-MODE MOSFET TRANSISTORS							
SC-89 (6 LEADS)							
Si1016X	20	1.25	1.8		0.75	0.50	0.30
	-20	2.70	-1.8		1.5	0.40	0.30
Si1035X	20	9.00	1.8		0.75	0.14	0.20
	-20	15.00	-1.8		1.5	0.16	0.30
Si1029X	60	3.0	4.5		0.75	0.33	0.25
	-60	8.0	-4.5		1.3	0.16	0.30
TYPE	V _{DS} (V)	r _{DS(on)} (ohm) MAX.	V _{GS(th)} MAX. (V)	t _{ON} (ns) MAX.	Q _g (nC) Typ	I _D MAX. (A)	P _D MAX. (W)
N- & P-CHANNEL QUADS 14-Pin Sidebraz (P) and Plastic (J)							
VQ3001J	±30	1/2	2.5/-4.5	30	38/60	±3	2
VQ3001P	±30	1/2	2.5/-4.5	30	38/60	±3	2
TYPE	NOMINAL FORWARD CURRENT (mA)	FORWARD CURRENT TOLERANCE(±%)	LIMITING VOLTAGE MAX. (V)	PEAK OPERATING VOLTAGE MIN. (V)	DYNAMIC IMPEDANCE MIN. (k Ω)	TYP. KNEE IMPEDANCE (k Ω)	
CURRENT REGULATOR DIODES - TO-206AA							
J500	0.24	20	1.2		50	4000	2500
J501	0.33	20	1.3		50	2200	1600
J502	0.43	20	1.5		50	1500	1100
J503	0.56	20	1.7		50	1200	800
J504	0.75	20	1.9		50	800	550
J505	1	20	2.1		50	500	400
J506	1.4	20	2.5		50	330	250
J507	1.8	20	2.8		50	200	190
J508	2.4	20	3.1		50	200	130
J509	3	20	3.5		50	150	90
J510	3.6	20	3.9		50	150	70
J511	4.7	20	4.2		50	120	50
CR160	1.6	10	1.65		100	475	400
CR180	1.8	10	1.75		100	420	340
CR200	2	10	1.85		100	395	280
CR220	2.2	10	1.95		100	370	250
CR 240	2.4	10	2		100	345	220

TYPE	NOMINAL FORWARD CURRENT (mA)	FORWARD CURRENT TOLERANCE (±%)	LIMITING VOLTAGE MAX. (V)	PEAK OPERATING VOLTAGE MIN. (V)	DYNAMIC IMPEDANCE MIN. (k Ω)	TYP. KNEE IMPEDANCE (k Ω)	
CR270 CR300 CR330 CR360 CR390 CR430 CR470	CURRENT REGULATOR DIODES - TO-206AA						
	2.7	10	2.15	100	320	190	
	3	10	2.25	100	300	160	
	3.3	10	2.35	100	280	140	
	3.6	10	2.5	100	265	130	
	3.9	10	2.6	100	255	120	
	4.3	10	2.75	100	245	100	
	4.7	10	2.9	100	235	90	
SST502 SST503 SST504 SST505 SST506 SST507 SST508 SST509 SST510 SST511	CURRENT REGULATOR DIODES - TO-236 (SOT-23)						
	0.43	20	1.5	45	1000	700	
	0.56	20	1.7	45	700	200	
	0.75	20	1.9	45	500	400	
	1	20	2.1	45	400	300	
	1.4	20	2.5	45	300	200	
	1.8	20	2.8	45	200	120	
	2.4	20	3.1	45	100	80	
	3	20	3.5	45	90	60	
	3.6	20	3.9	45	80	40	
	4.7	20	4.2	45	70	30	
TYPE	REVERSE CURRENT MAX. (pA)	BREAKDOWN VOLTAGE MIN.	BREAKDOWN VOLTAGE MAX.	FORWARD VOLTAGE MAX. (V)	REVERSE CAPACITANCE MAX. (pF)	FORWARD CURRENT MAX. (mA)	PACKAGE
PAD1 JPAD1 PAD5 SSTPAD5 JPAD50 PAD50 SSTPAD100	LOW LEAKAGE DIODES - CONFIGURATION - SINGLE						
	-1	-45	-120	1.5	0.8	50	TO-206AF*
	-5	-35	—	1.5	2	10	TO-226AA*
	-5	-45	-120	1.5	0.8	50	TO-206AF*/SOT-23
	-5	-35	—	1.5	2	10	TO-236
	-50	-35	—	1.5	2	10	TO-226AA*
	-50	-35	—	1.5	2	50	TO-206AF*
	-100	-35	—	1.5	2	10	TO-236AF*/SOT-23
DPAD1 DPAD5 SSTD PAD5 DPAD50 SSTD PAD100	LOW LEAKAGE DIODES - CONFIGURATION - DUAL						
	-1	-45	-120	1.5	0.8	50	TO-78*
	-5	-45	-120	1.5	0.8	50	TO-71*
	-5	-30	—	1.5	4	50	SO-8
	-50	-35	—	1.5	2	50	TO-71*
	-100	-30	—	1.5	4	50	SO-8
TYPE	BREAKDOWN VOLTAGE MIN. (V)	r _{DS(on)} (Ω) MIN.	MAX.	V _{GS(off)} (V) MIN.	MAX.	GATE LEAKAGE (pA)	PACKAGE
VCR2N VCR4N VCR7N	VOLTAGE CONTROLLED RESISTORS						
	-25	20	60	-3.5	-7	-5000	TO-206AA
	-25	200	600	-3.5	-7	-200	TO-206AA
	-25	4000	8000	-2.5	-5	-100	TO-206AF